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Citation: *J. Appl. Phys.* **92**, 6936 (2002); doi: 10.1063/1.1521801

View online: <http://dx.doi.org/10.1063/1.1521801>

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# Infrared-to-violet upconversion from $\text{Yb}^{3+}$ and $\text{Er}^{3+}$ codoped amorphous fluoride film prepared by pulsed laser deposition

Guanshi Qin, Weiping Qin,<sup>a)</sup> Shihua Huang, Changfeng Wu, Dan Zhao, Baojiu Chen, Shaozhe Lu, and E. Shulin

Laboratory of Excited States Processes, Chinese Academy of Sciences, Changchun 130021, People's Republic of China

(Received 26 March 2002; accepted 19 August 2002)

$\text{Yb}^{3+}$ – $\text{Er}^{3+}$  codoped amorphous  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$  film has been prepared by pulsed-laser deposition. Violet, green, red, and ultraviolet upconversion emissions were observed under infrared excitation at 988 nm. In comparison with the upconversion of the target, the violet and ultraviolet emissions are enhanced greatly. The enhancement is attributed to the diminishing of the cross relaxation:  $^4G_{11/2} \rightarrow ^4F_{9/2}$  ( $\text{Er}^{3+}$ ):  $^2F_{7/2} \rightarrow ^2F_{5/2}$  ( $\text{Yb}^{3+}$ ) induced by the decrement of the structure parameter  $\Omega_2$ . © 2002 American Institute of Physics. [DOI: 10.1063/1.1521801]

In recent years, short-wavelength solid-state lasers in the ultraviolet (UV) to green spectral range have attracted much attention due to a wide range of applications including optical data storage, color displays, and infrared sensors. The phenomenon of frequency upconversion by using the intrinsic energy level matching of certain rare-earth (RE) ions, as one of the available approaches exploring short-wavelength solid-state lasers, has been investigated widely during the past two decades.<sup>1–5</sup> Excited state absorption (ESA) and energy transfer (ET) can be a very efficient upconversion mechanism in RE doped materials. Huang *et al.*<sup>6</sup> reported upconversion in  $\text{LaF}_3:\text{Tm}^{3+}$  excited at 647.1 nm by ESA. Codoping of  $\text{Yb}^{3+}$  as a sensitizer has yielded a substantial improvement in the upconversion efficiency in  $\text{Tm}^{3+}$ ,  $\text{Pr}^{3+}$ ,  $\text{Ho}^{3+}$ , and  $\text{Er}^{3+}$  doped systems due to the efficient ET between the sensitizer and the pair or triads of RE ions.<sup>7–9</sup> In  $\text{Yb}^{3+}$ -sensitized RE doped materials, efficient infrared-to-UV or violet upconversion emissions at room temperature have been rarely investigated. Thrash *et al.*<sup>10</sup> reported upconverted UV luminescence in  $\text{BaYb}_{0.99}\text{Tm}_{0.01}\text{F}_8$  crystal. Therefore, studies on new approaches to obtain efficient UV and violet luminescence are very necessary and valuable due to the need of developing short-wavelength solid-state lasers.

Among the upconversion materials, bulk crystals, glasses, and fibers are quite attractive but high costs associated with the material preparation and device packaging as well as not integrating with semiconductors may limit their applications. Films, on the other hand, combine the advantages of bulk materials and the compactness of fibers, offering good prospects for upconversion devices. Upconversion waveguides can be fabricated by pulsed-laser deposition (PLD), which would allow directly integrating on the same chip the upconversion device with the pump source and other optoelectronic components.

In this communication, we report the upconversion emission properties of the  $\text{Yb}^{3+}$ – $\text{Er}^{3+}$  codoped  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$  (ZAPL) film. With the excitation of a 988-nm-laser-diode (LD), violet, green, red, and UV emissions were observed. The mechanism responsible for the enhancement of the violet and UV emission was also discussed.

953.6 nm radiation, from a Raman shifter pumped by the second harmonic of a Nd: YAG pulsed laser (pulse width 10 ns, repetition rate 10 Hz) was used as the light source for PLD. The Stokes-shifted line with the peak power of  $10^4$  W was focused on to the target<sup>11</sup> (ZAPL glass) in air at an incidence angle of about  $45^\circ$ . The substrate ( $\text{SiO}_2$  glass) was held 10–20 mm in front of the target at room temperature. The film is amorphous characterized by a transmission electron microscope (JEM-2010). X-ray photoelectron spectroscopy (XPS) data show that the components of the film are the same as those of the target. The upconverted emission spectra were measured under a power-adaptable 988-nm-LD excitation and were detected with a fluorescence spectrophotometer (Hitachi F-4500).

Figure 1(b) represents the upconversion emission spectrum of the film (pump power=800 mW). The emissions in the UV and visible ranges correspond to the following transitions:  $^4G_{11/2} \rightarrow ^4I_{15/2}$  ( $\sim 380$  nm);  $^2H_{9/2} \rightarrow ^4I_{15/2}$  ( $\sim 408$  nm);  $^2H_{11/2} \rightarrow ^4I_{15/2}$  ( $\sim 520$  nm);  $^4S_{3/2} \rightarrow ^4I_{15/2}$  ( $\sim 548$  nm); and  $^4F_{9/2} \rightarrow ^4I_{15/2}$  ( $\sim 650$  nm). Figure 1(a) shows the upconverted emission spectrum of the target (pump power=800 mW). It is obvious that the violet and UV emissions of the film are enhanced greatly, in comparison with that of the target.

For unsaturated upconversion, emission intensity,  $I_s$ , is proportional to  $I^n$ , where  $I$  is the intensity of the excitation light and  $n$ , the number of photons absorbed per upconverted photon emitted.<sup>12</sup> Intensity dependence of the upconversion emissions were obtained (data not shown):  $n=3.02$  for the emission at 408 nm;  $n=1.91$  for the 520 and 540 bands; and  $n=2.01$  for the 652 nm emission.

In  $\text{Yb}^{3+}$ – $\text{Er}^{3+}$  codoped systems, upconverted emission may be resulted from different processes, including multistep excited state absorption (ESA), energy transfer (ET) between

<sup>a)</sup> Author to whom correspondence should be addressed: Laboratory of Excited States Processes, Changchun Institute of Optics, Fine Mechanics and Physics, Chinese Academy of Sciences, Changchun 130021, People's Republic of China; electronic mail: wpqin@public.cc.jl.cn, gsqin@yahoo.com

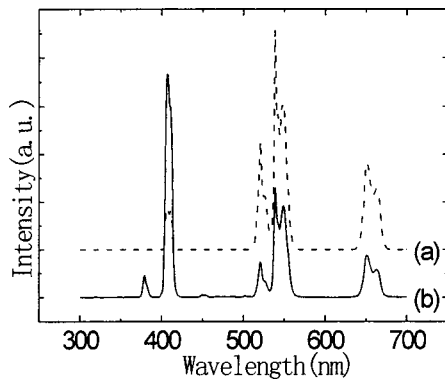


FIG. 1. Upconversion emission spectra of  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$ : (a) starting bulk material; (b) the PLD film.

excited neighboring  $\text{Er}^{3+}$  ions, and addition de photons par transfer d'énergie (APTE) between  $\text{Yb}^{3+}$  and  $\text{Er}^{3+}$ . Among these processes, APTE is the most efficient. Infrared to green ( $^2H_{11/2}$ ,  $^4S_{3/2} \rightarrow ^4I_{15/2}$  transitions) and to red ( $^4F_{9/2} \rightarrow ^4I_{15/2}$  transition) upconverted emissions in  $\text{Yb}^{3+}$ - $\text{Er}^{3+}$  codoped systems have been widely investigated.<sup>13</sup> Here, we focus our attention on the UV ( $\sim 380$  nm) and the violet ( $\sim 408$  nm) emissions.

As shown in Fig. 2, for the violet emission, there are two processes in populating the state  $^2H_{9/2}$ : (1) energy transfer  $^2F_{5/2} \rightarrow ^2F_{7/2}$  ( $\text{Yb}^{3+}$ ):  $^4F_{9/2} \rightarrow ^2H_{9/2}$  ( $\text{Er}^{3+}$ ) (ET1); and (2) energy transfer  $^2F_{5/2} \rightarrow ^2F_{7/2}$  ( $\text{Yb}^{3+}$ ):  $^4S_{3/2} \rightarrow ^2G_{7/2}$  ( $\text{Er}^{3+}$ ) (ET2), followed by fast cascading relaxation to the  $^4G_{11/2}$  and  $^2H_{9/2}$  states. On the other hand, the following cross relaxation (CR),<sup>13</sup>  $^4G_{11/2} \rightarrow ^4F_{9/2}$  ( $\text{Er}^{3+}$ ):  $^2F_{7/2} \rightarrow ^2F_{5/2}$  ( $\text{Yb}^{3+}$ ), would depopulate the state  $^4G_{11/2}$ . Figure 3 represents the excitation spectra of the target (a)  $\lambda_{\text{mon}} = 652$  nm, (b)  $\lambda_{\text{mon}} = 540$  nm. The results show that the excitation of the state  $^4G_{11/2}$  would produce intense red emission which is attributed to the intense CR process:  $^4G_{11/2} \rightarrow ^4F_{9/2}$  ( $\text{Er}^{3+}$ ):  $^2F_{7/2} \rightarrow ^2F_{5/2}$  ( $\text{Yb}^{3+}$ ), and weak green emission from the relaxation of the high levels. In our film, XPS data showed that the RE concentration was not changed during PLD. Therefore, the most possible mechanism responsible for the enhancement of the violet emission is the change of structure coupled with RE ions during PLD.

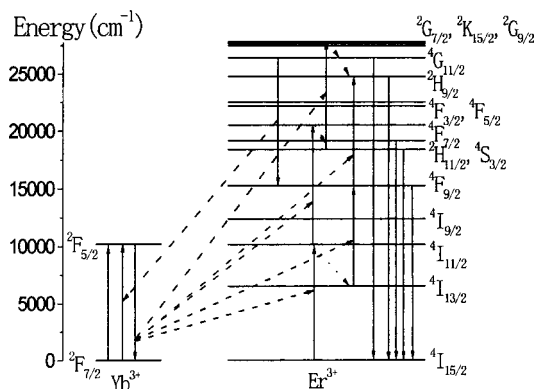


FIG. 2. Schematic diagram of  $\text{Yb}^{3+}$ -sensitized  $\text{Er}^{3+}$  upconversion in  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$  film under 988 nm excitation.

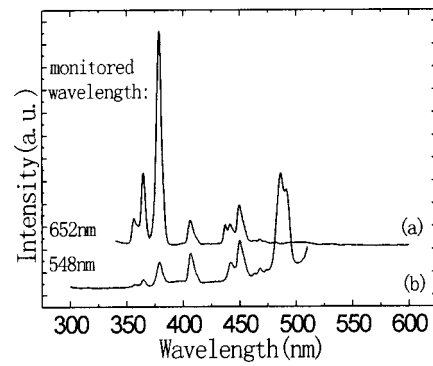


FIG. 3. Excitation spectra of the target (a)  $\lambda_{\text{mon}} = 652$  nm, (b)  $\lambda_{\text{mon}} = 540$  nm.

For the  $\text{Tm}^{3+}$  ion, since the  $\langle \|U^{(2)}\| \rangle^2$  of the  $^1D_2 \rightarrow ^3F_4$  transition is large, the branching ratio of the blue 451 nm emission,  $\beta_{451}$  would be largely enhanced by the increased value of  $\Omega_2$ , which reflects the asymmetry of the ligand field.<sup>14</sup> In addition,  $\beta_{451} + \beta_{361} \approx 1$ , where  $\beta_{361}$  is the branching ratio of the  $^1D_2 \rightarrow ^3H_6$  transition,<sup>2</sup> so the fluorescence intensity ration  $\sigma = I_{451 \text{ nm}}(^1D_2 \rightarrow ^3F_4 \text{ transition}) / [I_{361 \text{ nm}}(^1D_2 \rightarrow ^3H_6 \text{ transition}) + I_{451 \text{ nm}}(^1D_2 \rightarrow ^3F_4 \text{ transition})] \approx \beta_{451}$  of  $\text{Tm}^{3+}$  will be influenced by the change of structure parameter  $\Omega_2$ . In order to clarify the change of the structure during PLD,  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Tm}_{0.01}\text{F}_{2.37}$  film was also prepared at the same PLD conditions. Figure 4 shows that the upconversion emission spectra of (a) the film and (b) the target excited at 988 nm (pump power = 800 mW). From Fig. 4, we obtained  $\sigma = 0.95$  for the target, and  $\sigma = 0.55$  for the film. Decreasing of  $\sigma$  shows that the structure parameter  $\Omega_2$  becomes smaller during PLD.

Considering the reduced matrix elements of the  $\text{Er}^{3+}$ :  $^4G_{11/2}$  level<sup>15</sup> (as shown in Table I) and the Einstein transition parameter formula

$$A_{j''j'} = \frac{64\pi^4 \nu^3 e^2}{3hc^2} \cdot \frac{1}{2J''+1} \cdot \frac{n(n^2+2)^2}{9} \sum_{\lambda} \Omega_{\lambda} U_{JJ'}^{(\lambda)}$$

[where  $\Omega_{\lambda}$  ( $\lambda = 2, 4, 6$ ) is the structure parameter,  $U_{JJ'}^{(\lambda)}$  the matrix element], the transition rate from  $^4G_{11/2}$  to  $^4F_{9/2}$  will be precluded with decreasing the structure parameter  $\Omega_2$ , which will enhance the  $^4G_{11/2} \rightarrow ^4I_{15/2}$  transition and also

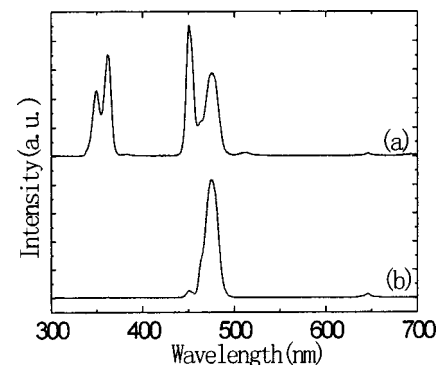


FIG. 4. Upconversion emission spectra of  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Tm}_{0.01}\text{F}_{2.37}$ : (a) the PLD film; (b) the starting bulk material.

TABLE I. Reduced matrix elements of the  $\text{Er}^{3+}: {}^4G_{11/2}$  level.

Transitions of $\text{Er}^{3+}$	$(U^{(2)})^2$	$(U^{(4)})^2$	$(U^{(6)})^2$
${}^4G_{11/2} \rightarrow {}^4F_{9/2}$	0.4283	0.0372	0.0112

make the state  ${}^2H_{9/2}$  populated efficiently by the nonradiation relaxation from the  ${}^4G_{11/2}$  level. Therefore, we conclude that the decrement of the structure parameter  $\Omega_2$  during PLD lead to the enhancement of the violet upconversion luminescence in the film.

In conclusion, a scheme for the conversion of IR radiation into violet emission centered at 408 nm in a  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$  film was reported. The results of  $\text{Tm}^{3+}$  as a structure probe indicate that the structure parameter  $\Omega_2$  becomes smaller during PLD, which preclude the depopulation process of the state  ${}^4G_{11/2}: {}^4G_{11/2} \rightarrow {}^4F_{9/2}$  ( $\text{Er}^{3+}$ ):  ${}^2F_{7/2} \rightarrow {}^2F_{5/2}$  ( $\text{Yb}^{3+}$ ). Therefore, the intense violet upconversion luminescence was obtained in  $\text{Zn}_{0.3}\text{Al}_{0.25}\text{Pb}_{0.3}\text{Li}_{0.09}\text{Yb}_{0.1}\text{Er}_{0.01}\text{F}_{2.37}$  film.

This research was supported by State Key Project of Basic Research.

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